



# TSD965L

## Low V<sub>ce(sat)</sub> NPN Transistor

TO-92



Pin assignment:

1. Emitter
2. Collector
3. Base

**BV<sub>CEO</sub> = 10V**

**I<sub>C</sub> = 5A**

**V<sub>CE(SAT)</sub>, = 0.23V(typ.) @I<sub>C</sub> / I<sub>B</sub> = 3A / 60mA**

### Features

- ✧ Low V<sub>CE(SAT)</sub>.
- ✧ High current capability
- ✧ High allowable power dissipation

### Structure

- ✧ Epitaxial planar type.

### Ordering Information

Part No.	Packing	Package
TSD965LCT B0	Bulk Pack	TO-92
TSD965LCT A3	Ammo Pack	

### Absolute Maximum Rating (T<sub>a</sub> = 25 °C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V <sub>CBO</sub>	15V	V
Collector-Emitter Voltage	V <sub>CEO</sub>	10V	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Collector Current	DC	5	A
	Pulse	9 (note 1)	
Collector Power Dissipation	P <sub>D</sub>	0.75 (note 2)	W
Operating Junction Temperature	T <sub>J</sub>	+150	°C
Operating Junction and Storage Temperature Range	T <sub>STG</sub>	- 55 to +150	°C

Note: 1. Single pulse, P<sub>w</sub> = 350uS, Duty <= 2%

2. When a device is mounted on a glass epoxy board, Measuring 35mm x 30mm x 1mm

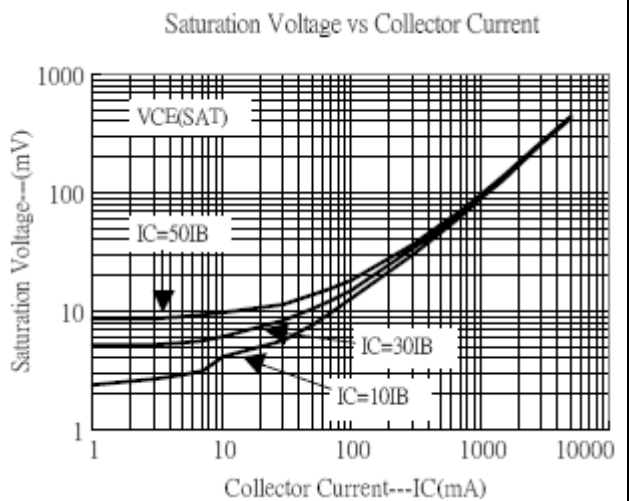
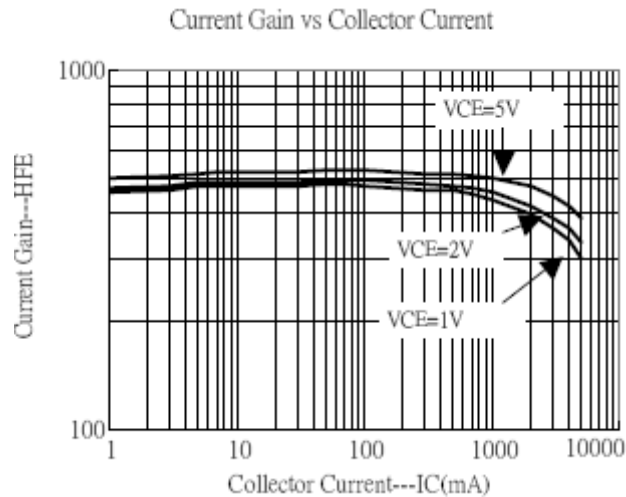
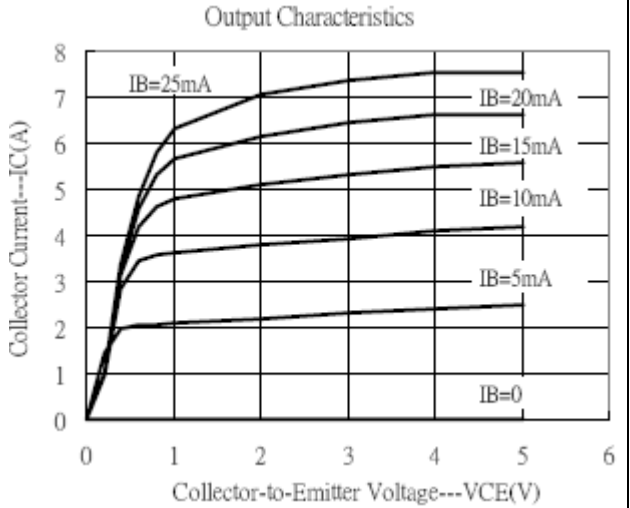
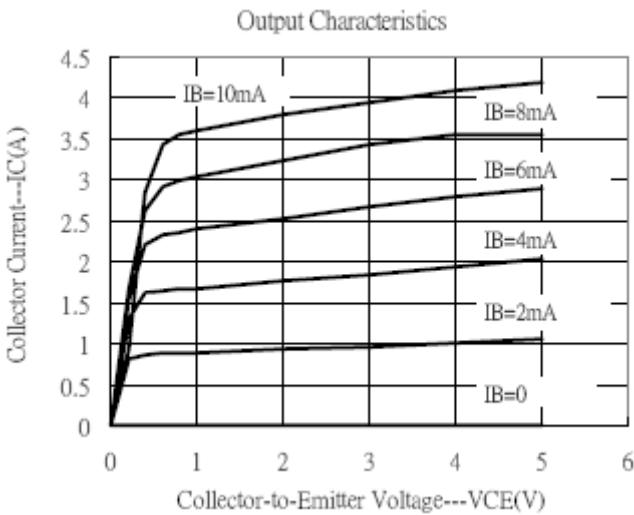
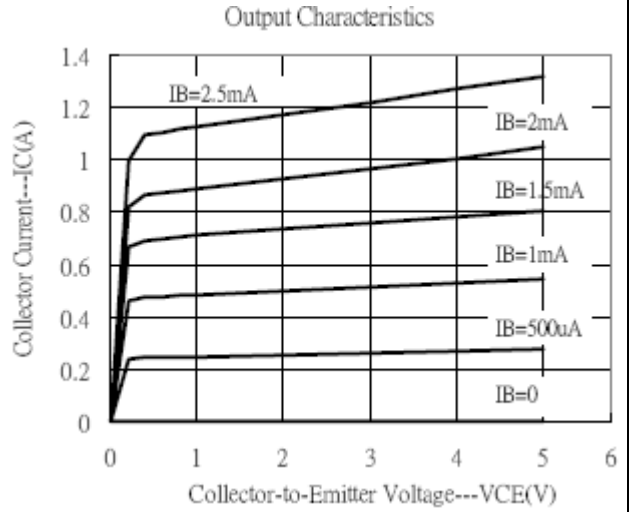
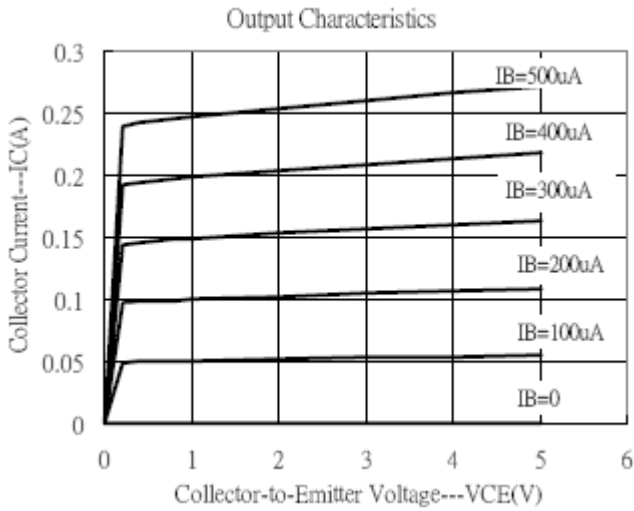
### Electrical Characteristics

T<sub>a</sub> = 25 °C unless otherwise noted

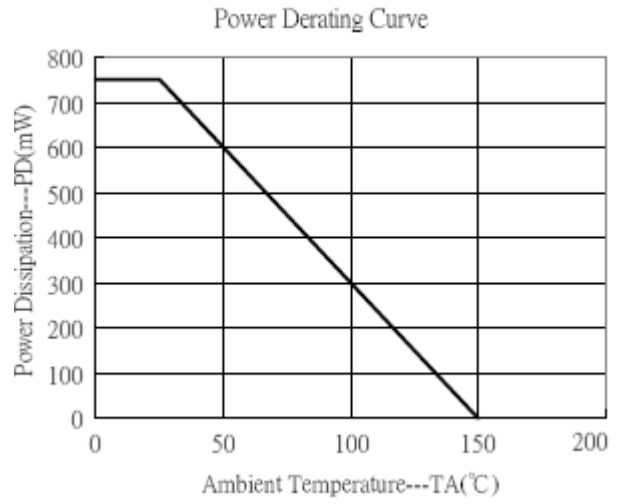
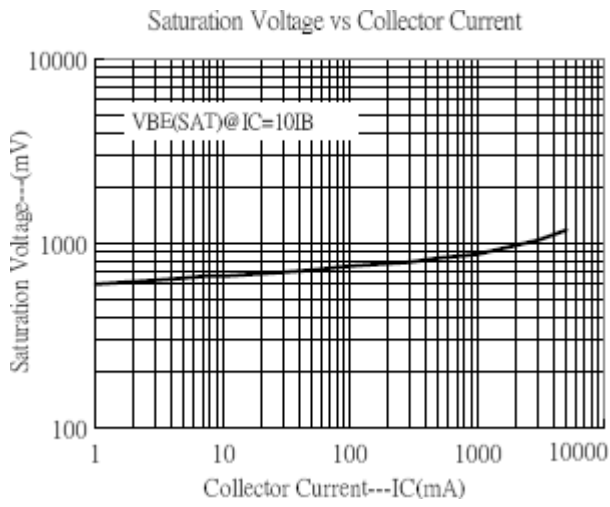
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
<b>Static</b>						
Collector-Base Voltage	I <sub>C</sub> = 100uA, I <sub>E</sub> = 0	BV <sub>CBO</sub>	15	--	--	V
Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA, I <sub>B</sub> = 0	BV <sub>CEO</sub>	10	--	--	V
Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10uA, I <sub>C</sub> = 0	BV <sub>EBO</sub>	7	--	--	V
Collector Cutoff Current	V <sub>CB</sub> = 15V, I <sub>E</sub> = 0	I <sub>CBO</sub>	--	--	100	nA
Emitter Cutoff Current	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0	I <sub>EBO</sub>	--	--	100	nA
Collector-Emitter Saturation Voltage	I <sub>C</sub> / I <sub>B</sub> = 1.5A / 30mA	V <sub>CE(SAT)</sub>	--	--	0.18	V
	I <sub>C</sub> / I <sub>B</sub> = 3.0A / 60mA	V <sub>CE(SAT)</sub>	--	0.23	0.35	V
Base-Emitter Saturation Voltage	I <sub>C</sub> / I <sub>B</sub> = 1.5A / 30mA	V <sub>CE(SAT)</sub>	--	0.95	1.2	V
DC Current Transfer Ratio	V <sub>CE</sub> = 2V, I <sub>C</sub> = 0.5A	h <sub>FE</sub>	400	--	--	
	V <sub>CE</sub> = 2V, I <sub>C</sub> = 2.0A	h <sub>FE</sub>	390	--	820	
	V <sub>CE</sub> = 2V, I <sub>C</sub> = 5.0A	h <sub>FE</sub>	185	--	--	
Transition Frequency	V <sub>CE</sub> = 6V, I <sub>C</sub> = 50mA, f = 100MHz	f <sub>T</sub>	--	170	--	MHz
Output Capacitance	V <sub>CB</sub> = 10V, f = 1MHz	C <sub>ob</sub>	--	25	--	pF

Note : pulse test: pulse width <=380uS, duty cycle <=2%

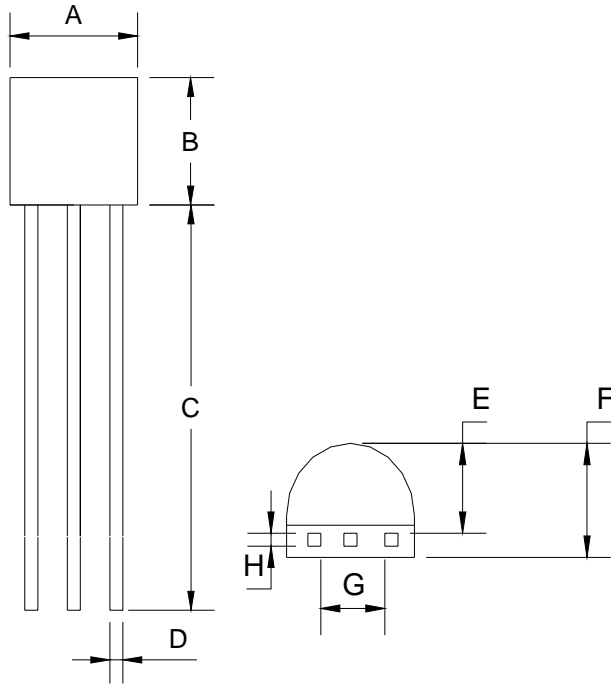
## Electrical Characteristics Curve



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## TO-92 Mechanical Drawing



TO-92 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.70	0.169	0.185
B	4.30	4.70	0.169	0.185
C	14.30(typ)		0.563(typ)	
D	0.43	0.49	0.017	0.019
E	2.19	2.81	0.086	0.111
F	3.30	3.70	0.130	0.146
G	2.42	2.66	0.095	0.105
H	0.37	0.43	0.015	0.017